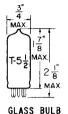
### TUNG-SOL -

# DIODE PENTODE MINIATURE TYPE



COATED FILAMENT

1.4 VOLTS 25 MA.
AC OR DC

ANY MOUNTING POSITION



BOTTOM VIEW
MINIATURE BUTTON
7 PIN BASE
6AU

THE 1AF5 IS A FILAMENTARY TYPE DIODE PENTODE VOLTAGE AMPLIFIER USING THE 7 PIN MINIATURE CONSTRUCTION. IT IS DESIGNED SPECIFICALLY FOR USE IN PORTABLE RECEIVERS AS A DETECTOR AND AF AMPLIFIER. THE FILAMENT POWER CONSUMPTION HAS BEEN CUT IN HALF WITH RESPECT TO TUBES PREVIOUSLY USED IN THIS SERVICE.

### DIRECT INTERELECTRODE CAPACITANCES

	WITHOUT Shield	WITH A	
GRID TO PLATE: (G1 TO P)	0.2	0.2	μμf
INPUT: G, TO (F&G3+G2)	2.3	2.5	į પાય f
OUTPUT: P TO (F&G3+G2)	2.4	4.3	μμf
DIODE TO GRID #1: (P1 TO G1) MAX.	0.03	0.03	μμ f

Ashield #316 connected to PIN #1.

## RATINGS INTERPRETED ACCORDING TO RMA STANDARD M8-210

FILAMENT VOLTAGE	1.4	VOLTS
MAXIMUM PLATE VOLTAGE	110	VOLTS
MAXIMUM GRID #2 VOLTAGE	110	VOLTS
MAXIMUM POSITIVE GRID #1 VOLTAGE	0	VOLTS
MAXIMUM CATHODE CURRENT	2.5	MA.
MAXIMUM DIODE CURRENT FOR CONTINUOUS OPERATION	0.25	MA.

#### TYPICAL OPERATING CONDITIONS AND CHARACTERISTICS

### CLASS A1 AMPLIFIER

FILAMENT VOLTAGE   1.4   1.4   VOLTS				
PLATE VOLTAGE         67.5         90         VOLTS           GRID #2 VOLTAGE         67.5         90         VOLTS           GRID #1 VOLTAGE         0         0         VOLTS           PLATE RESISTANCE         2.3         2         MEGOHN           TRANSCONDUCTANCE         500         600         μΜΗΟS           PLATE CURRENT         0.7         1.1         MA.           GRID #2 CURRENT         0.25         0.4         MA.           GRID #1 VOLTAGE FOR Gm = 10 μΜΗΟS         -2.5         -3.5         VOLTS           AVERAGE DIODE CURRENT WITH 10 VOLTS         VOLTS	FILAMENT VOLTAGE	1.4	1.4	VOLTS
GRID #2 VOLTAGE 67.5 90 VOLTS GRID #4 VOLTAGE 0 0 VOLTS PLATE RESISTANCE 2.3 2 MEGOHN TRANSCONDUCTANCE 500 600 µMHOS PLATE CURRENT 0.7 1.1 MA. GRID #2 CURRENT 0.25 0.4 MA. GRID #4 VOLTAGE FOR Gm = 40 µMHOS -2.5 -3.5 VOLTS AVERAGE DIODE CURRENT WITH 40 VOLTS	FILAMENT CURRENT	25	25	MA.
GRID #1 VOLTAGE  PLATE RESISTANCE  TRANSCONDUCTANCE  PLATE CURRENT  GRID #2 CURRENT  GRID #2 VOLTAGE FOR Gm = 10 µMHOS  AVERAGE DIODE CURRENT WITH 10 VOLTS	PLATE VOLTAGE	67.5	90	VOLTS
PLATE RESISTANCE 2.3 2 MEGONN TRANSCONDUCTANCE 500 600 µMHOS PLATE CURRENT 0.7 1.1 MA. GRID #2 CURRENT 0.25 0.4 MA. GRID #4 VOLTAGE FOR Gm = 10 µMHOS -2.5 -3.5 VOLTS AVERAGE DIODE CURRENT WITH 10 VOLTS	GRID #2 VOLTAGE	67.5	90	VOLTS
TRANSCONDUCTANCE 500 600 µMHOS PLATE CURRENT 0.7 1.1 MA. GRID #2 CURRENT 0.25 0.4 MA. GRID #4 VOLTAGE FOR Gm = 10 µMHOS -2.5 -3.5 VOLTS AVERAGE DIODE CURRENT WITH 10 VOLTS	GRID #1 VOLTAGE	0	0	VOLTS
PLATE CURRENT 0.7 1.1 MA.  GRID #2 CURRENT 0.25 0.4 MA.  GRID #4 VOLTAGE FOR G <sub>m</sub> = 10 µMHOS -2.5 -3.5 VOLTS  AVERAGE DIODE CURRENT WITH 10 VOLTS	PLATE RESISTANCE	2.3	2	MEGOHMS
GRID #2 CURRENT 0.25 0.4 MA.  GRID #4 VOLTAGE FOR G <sub>m</sub> = 10 µMHOS -2.5 -3.5 VOLTS  AVERAGE DIODE CURRENT WITH 10 VOLTS	TRANSCONDUCTANCE	500	600	μ <b>м</b> Hos
GRID #4 VOLTAGE FOR Gm = 40 µMHOS -2.5 -3.5 VOLTS  AVERAGE DIODE CURRENT WITH 40 VOLTS	PLATE CURRENT	0.7	1.1	MA.
AVERAGE DIODE CURRENT WITH 40 VOLTS	GRID #2 CURRENT	0.25	0.4	MA.
	GRID #1 VOLTAGE FOR Gm = 10 MHOS	-2.5	-3.5	VOLTS
	AVERAGE DIODE CURRENT WITH 40 VOLTS DC APPLIED	0.7	0.7	MA.